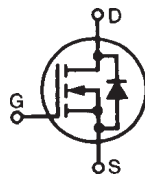


PolarHV™ HiperFET Power MOSFET

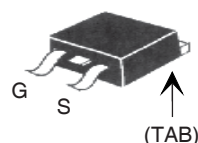
IXFA14N60P
IXFP14N60P
IXFH14N60P

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

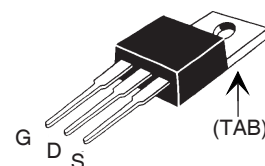


$V_{DSS} = 600V$
 $I_{D25} = 14A$
 $R_{DS(on)} \leq 550m\Omega$
 $t_{rr} \leq 200ns$

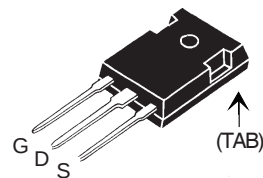
TO-263



TO-220



TO-247



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$ $R_{GS} = 1M\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	14	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	42	A
I_A	$T_C = 25^\circ C$	14	A
E_{AS}	$T_C = 25^\circ C$	900	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	300	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nmlb.in.
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5mA$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1	450		550 m Ω

Features

- International standard packages
- Avalanche rated

Advantages

- Easy to mount
- Space savings
- High power density

Applications:

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

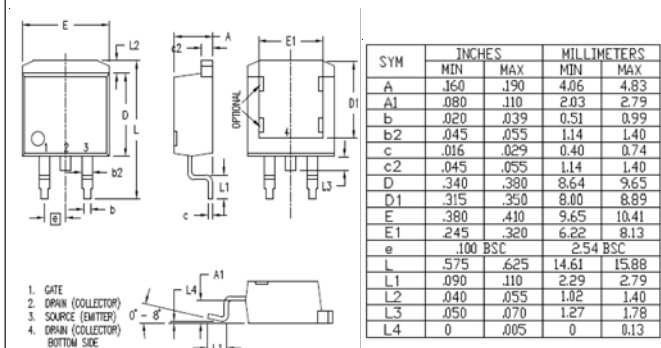
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	7	13	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		2500	pF
C_{oss}			215	pF
C_{rss}			13	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		23	ns
t_r			27	ns
$t_{d(off)}$			70	ns
t_f			26	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		36	nC
Q_{gs}			16	nC
Q_{gd}			12	nC
R_{thJC}				0.42°C/W
R_{thCH}	(TO-220)	0.50		$^\circ\text{C/W}$
	(TO-247)	0.21		$^\circ\text{C/W}$

Source-Drain Diode

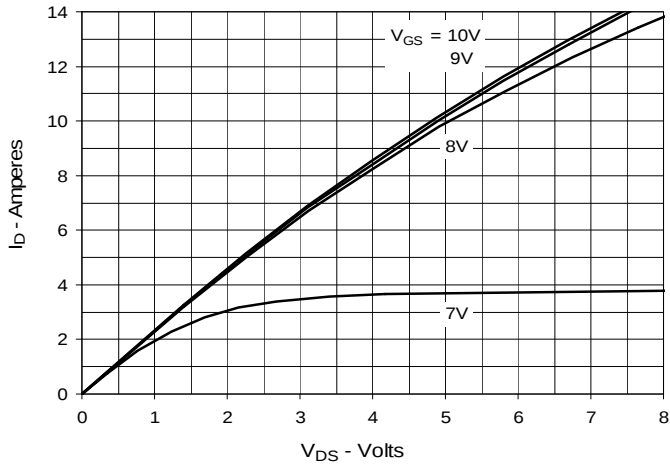
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			14 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			42 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 14\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$			200 ns
I_{RM}		6.0		A
Q_{RM}		0.6		nC

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

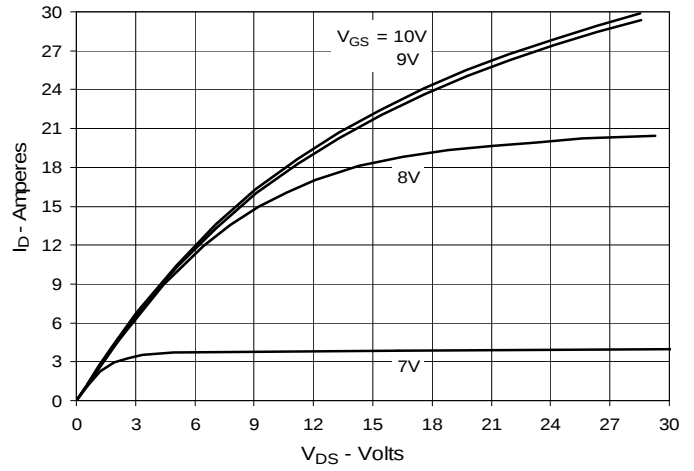
TO-263 (IXFA) Outline



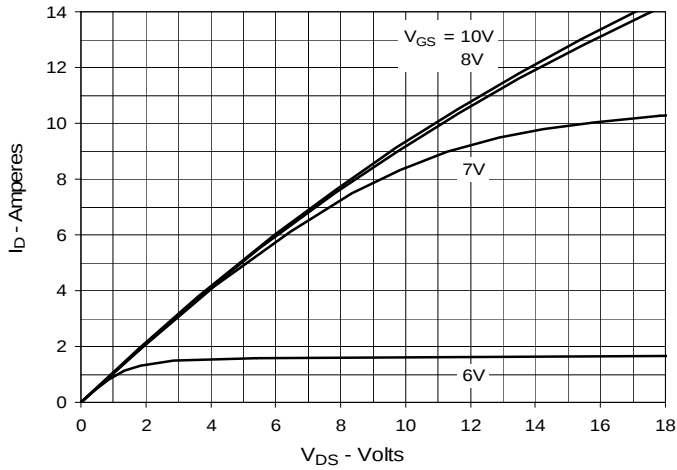
**Fig. 1. Output Characteristics
@ 25°C**



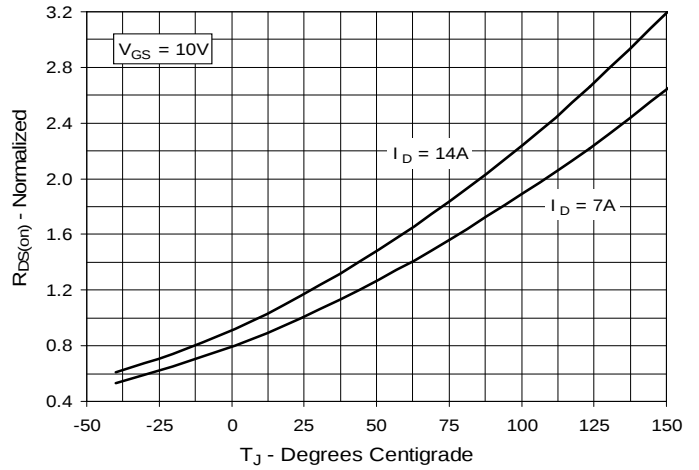
**Fig. 2. Extended Output Characteristics
@ 25°C**



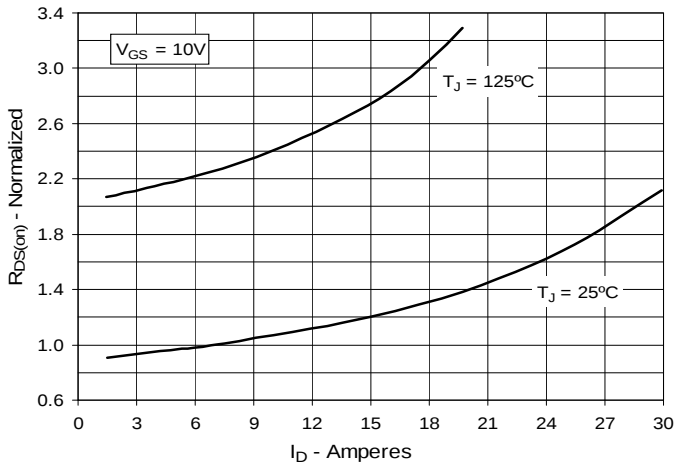
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 7A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 7A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

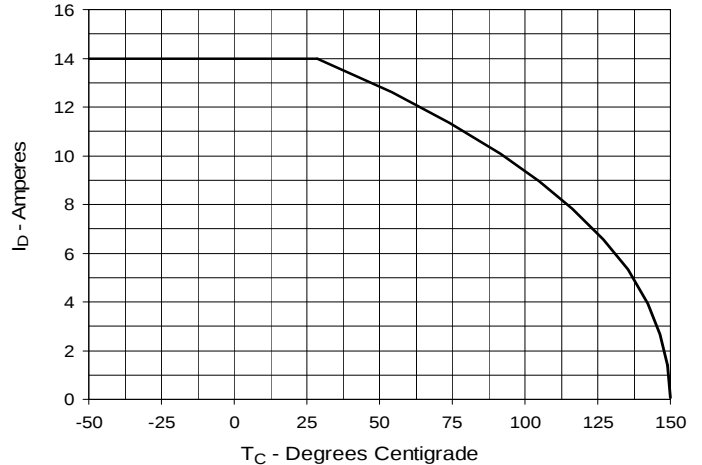


Fig. 7. Input Admittance

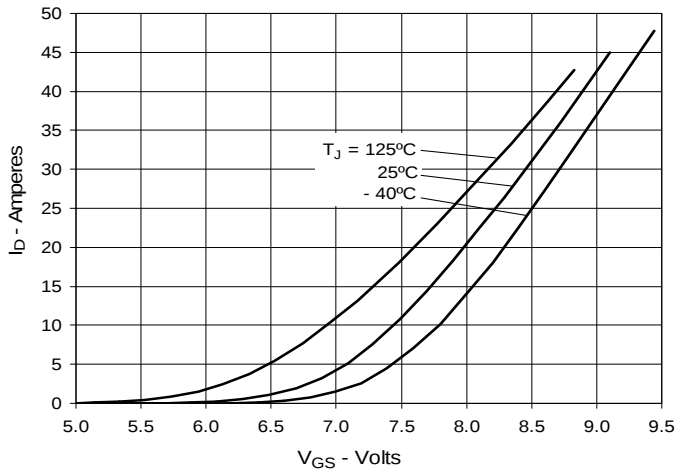


Fig. 8. Transconductance

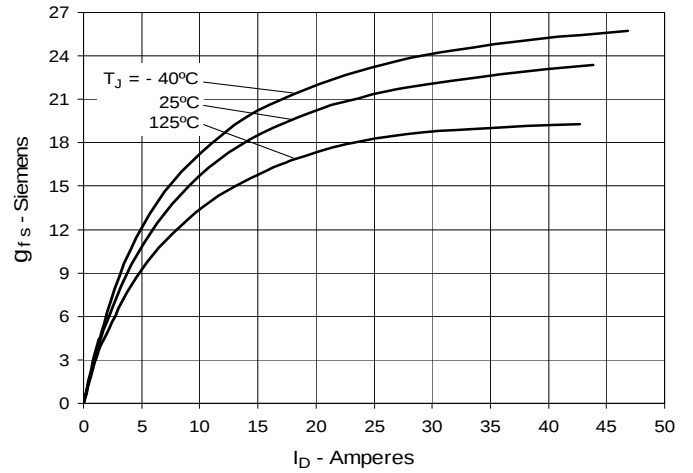


Fig. 9. Forward Voltage Drop of Intrinsic Diode

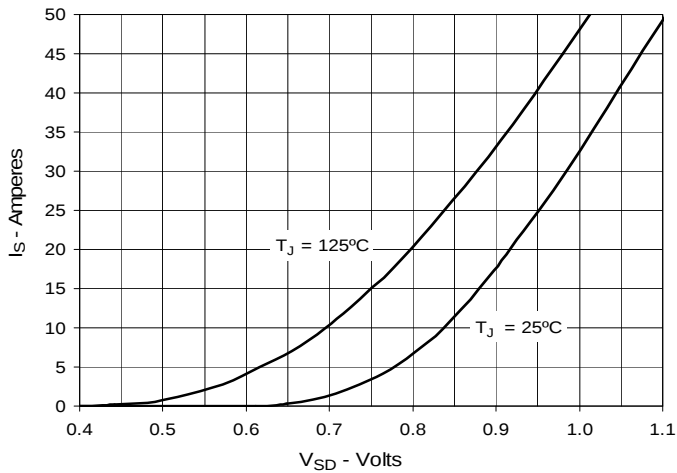


Fig. 10. Gate Charge

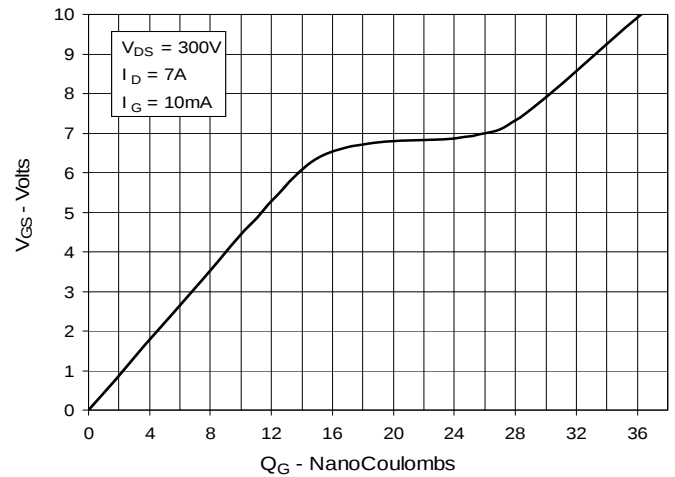


Fig. 11. Capacitance

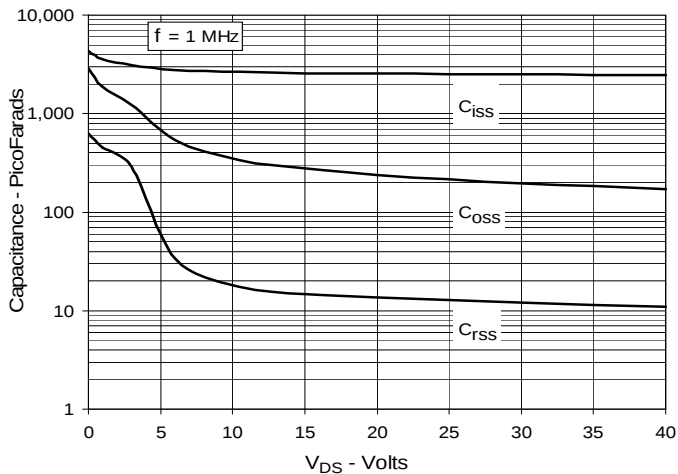


Fig. 12. Forward-Bias Safe Operating Area

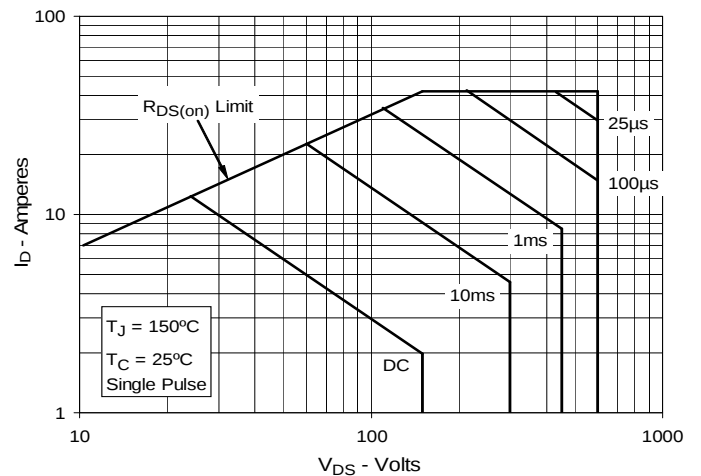


Fig. 13. Maximum Transient Thermal Impedance

